NSN 5962-01-441-2112

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View Online at https://aerobasegroup.com/nsn/5962-01-441-2112

Body Length:
1.290 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
0.225 inches
Maximum Power Dissipation Rating:
1.02 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
B-1b
Features Provided:
Bipolar and burn in, mil-std-883, class b and electrostatic sensitive and hermetically sealed and high impedance and monolithic and
programmed and schottky and tested to mil-std-883 and w/active pull-up and 3-state output
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
13 input
Criticality Code Justification:
Cbbl
Case Outline Source And Designator:
D-3 mil-m-38510
Current Rating Per Characteristic:
185.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital (programmed 512x8)
Voltage Rating And Type Per Characteristic:
-1.5 volts input and 5.5 volts input and -0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
90.00 nanoseconds access and 50.00 nanoseconds propagation delay time, low to high level output
Memory Device Type:
Prom

Special Features:

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Test	Data	Docum	ent
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96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A458a0